

# AP30N03K

## N-Channel Power MOSFET

### Description

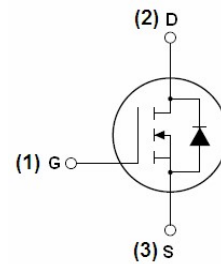
The AP30N03K uses advanced trench technology and design to provide excellent  $R_{DS(ON)}$  with low gate charge. It can be used in a wide variety of applications.

### General Features

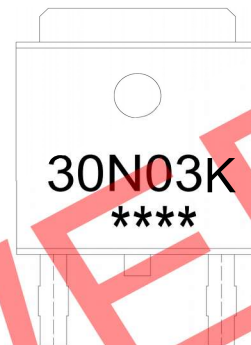
- $V_{DS} = 30V, I_D = 30A$   
 $R_{DS(ON)} < 20m\Omega @ V_{GS} = 10V$   
 $R_{DS(ON)} < 26m\Omega @ V_{GS} = 5V$
- High density cell design for ultra low  $R_{dson}$
- Fully characterized Avalanche voltage and current
- Good stability and uniformity with high  $E_{AS}$
- Excellent package for good heat dissipation
- Special process technology for high ESD capability

### Application

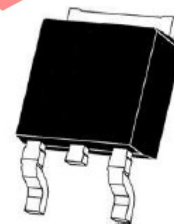
- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible Power Supply



Schematic diagram



Marking and pin assignment



TO-252-2L top view

### Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
30N03K	AP30N03K	TO-252-2L	-	-	-

### Absolute Maximum Ratings ( $T_C = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	30	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Drain Current-Continuous	$I_D$	30	A
Drain Current-Continuous( $T_C = 100^\circ C$ )	$I_D(100^\circ C)$	22	A
Pulsed Drain Current	$I_{DM}$	60	A
Maximum Power Dissipation	$P_D$	45	W
Derating factor		0.4	W/ $^\circ C$
Single pulse avalanche energy <sup>(Note 5)</sup>	$E_{AS}$	40	mJ
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 175	$^\circ C$

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### Thermal Characteristic

Thermal Resistance, Junction-to-Case <sup>(Note 2)</sup>	$R_{\theta JC}$	2.5	°C/W
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### Electrical Characteristics ( $T_c=25^\circ\text{C}$ unless otherwise noted)

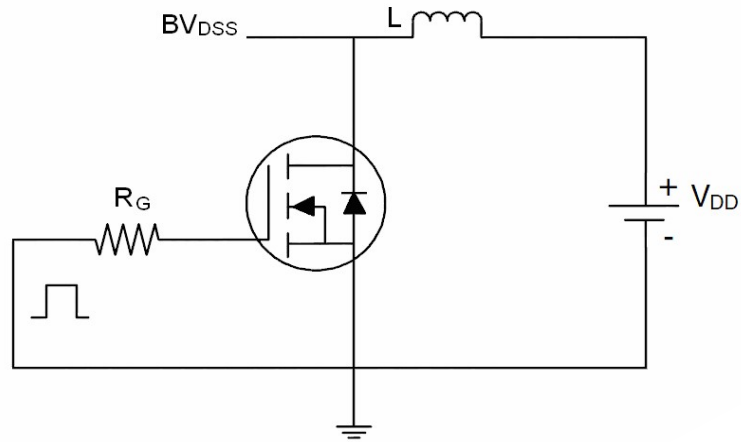
Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=250\mu A$	30	33	-	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=30V, V_{GS}=0V$	-	-	1	$\mu A$
Gate-Body Leakage Current	$I_{GSS}$	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	$\pm 100$	nA
<b>On Characteristics</b> <sup>(Note 3)</sup>						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1	1.6	3	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=15A$	-	15	20	m $\Omega$
		$V_{GS}=5V, I_D=20A$	-	20	24	
Forward Transconductance	$g_{FS}$	$V_{DS}=5V, I_D=10A$	10	-	-	S
<b>Dynamic Characteristics</b> <sup>(Note 4)</sup>						
Input Capacitance	$C_{iss}$	$V_{DS}=15V, V_{GS}=0V,$ $F=1.0\text{MHz}$	-	350	-	PF
Output Capacitance	$C_{oss}$		-	55	-	PF
Reverse Transfer Capacitance	$C_{rss}$		-	35	-	PF
<b>Switching Characteristics</b> <sup>(Note 4)</sup>						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=15V, I_D=1A$ $V_{GS}=10V, R_{GEN}=3.3\Omega$	-	8	-	nS
Turn-on Rise Time	$t_r$		-	7	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	15	-	nS
Turn-Off Fall Time	$t_f$		-	5	-	nS
Total Gate Charge	$Q_g$	$V_{DS}=15V, I_D=8A,$ $V_{GS}=4.5V$	-	4.1	-	nC
Gate-Source Charge	$Q_{gs}$		-	1.1	-	nC
Gate-Drain Charge	$Q_{gd}$		-	2.5	-	nC
<b>Drain-Source Diode Characteristics</b>						
Diode Forward Voltage <sup>(Note 3)</sup>	$V_{SD}$	$V_{GS}=0V, I_S=1A$	-	0.85	1.2	V
Diode Forward Current <sup>(Note 2)</sup>	$I_S$		-	-	50	A
Reverse Recovery Time	$t_{rr}$	$T_J = 25^\circ\text{C}, I_F = 10A$ $di/dt = 100A/\mu s$ <sup>(Note 3)</sup>	-	15	30	nS
Reverse Recovery Charge	$Q_{rr}$		-	14	28	nC
Forward Turn-On Time	$t_{on}$	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

### Notes:

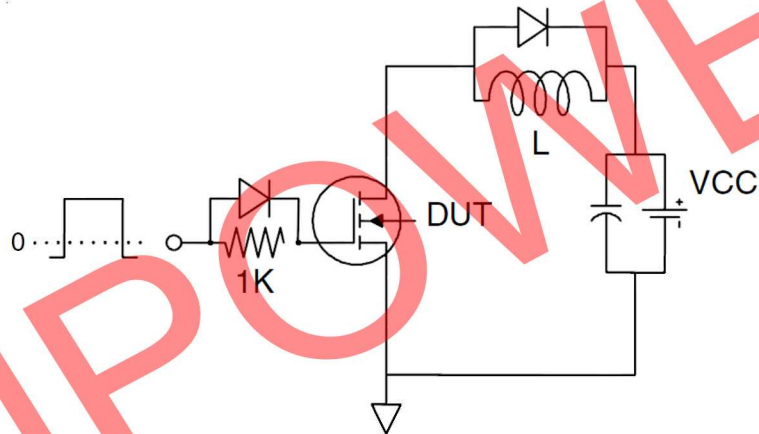
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board,  $t \leq 10$  sec.
3. Pulse Test: Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$ .
4. Guaranteed by design, not subject to production
5. EAS condition:  $T_J=25^\circ\text{C}$ ,  $V_{DD}=15V, V_G=10V, L=0.1\text{mH}, R_g=25\Omega$

## Test circuit

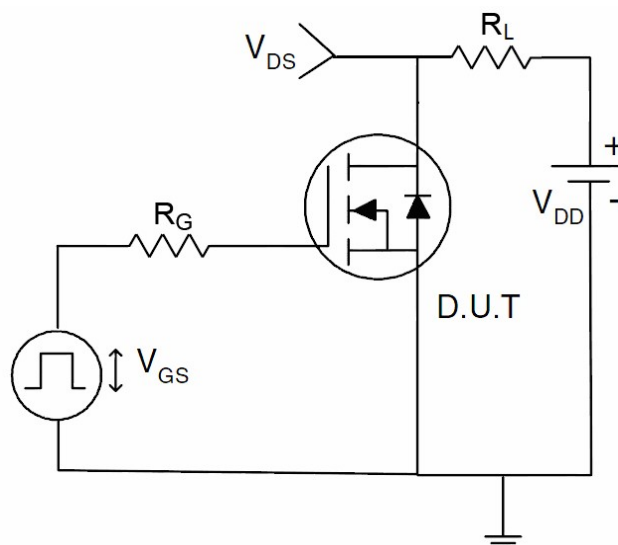
### 1) $E_{AS}$ test Circuits



### 2) Gate charge test Circuit:

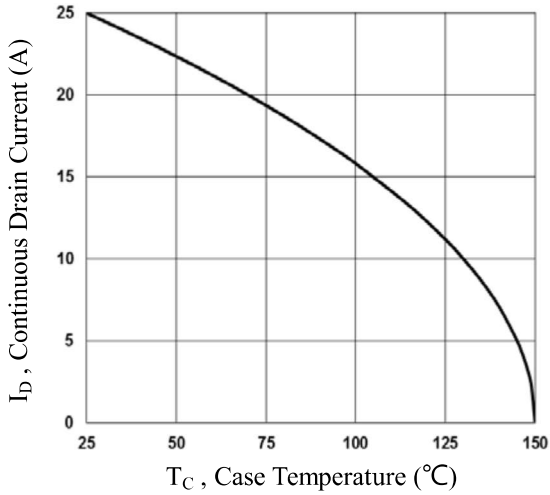


### 3) Switch Time Test Circuit:

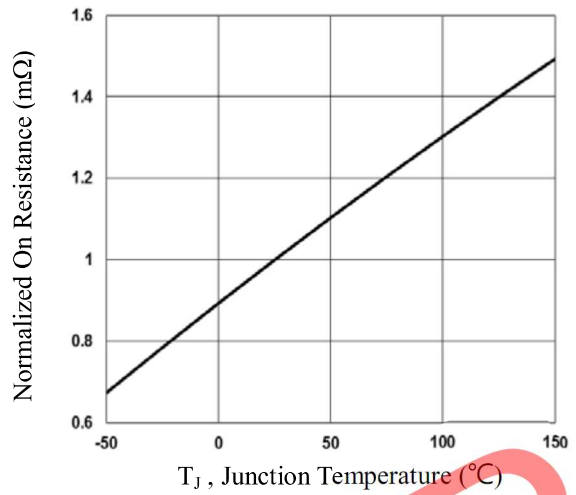


**N-Channel Power MOSFET**

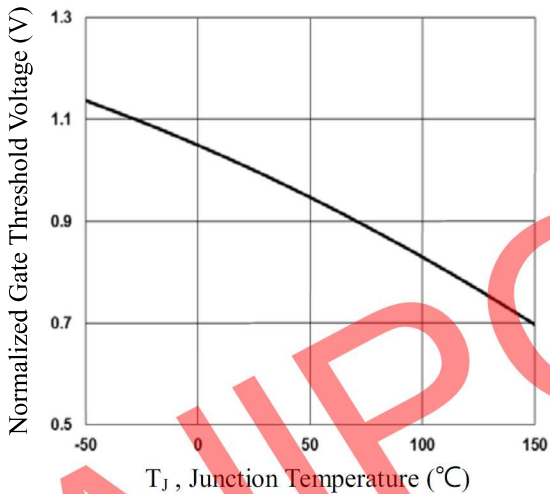
**Typical Electrical and Thermal Characteristics (Curves)**



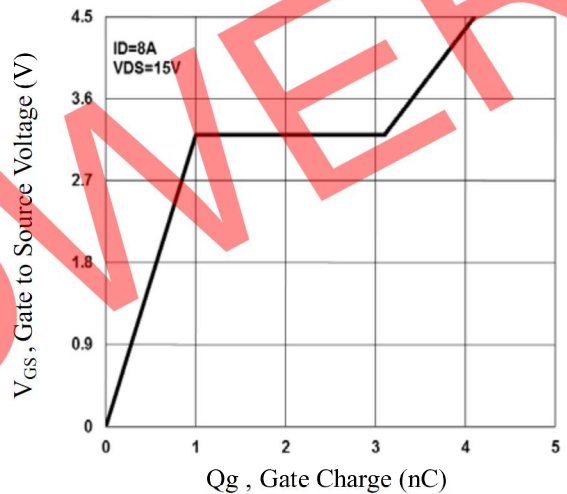
**Fig.1 Continuous Drain Current vs.  $T_c$**



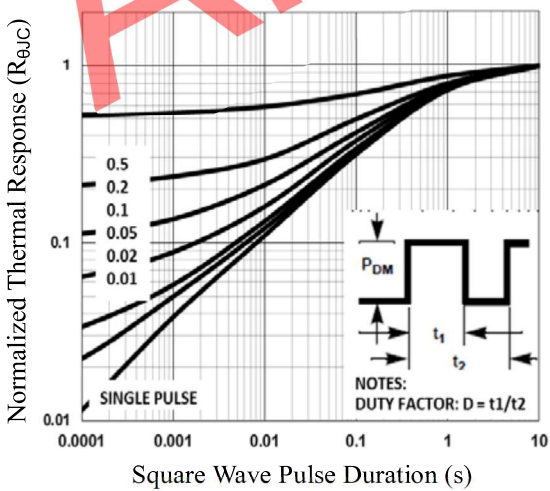
**Fig.2 Normalized RDSON vs.  $T_j$**



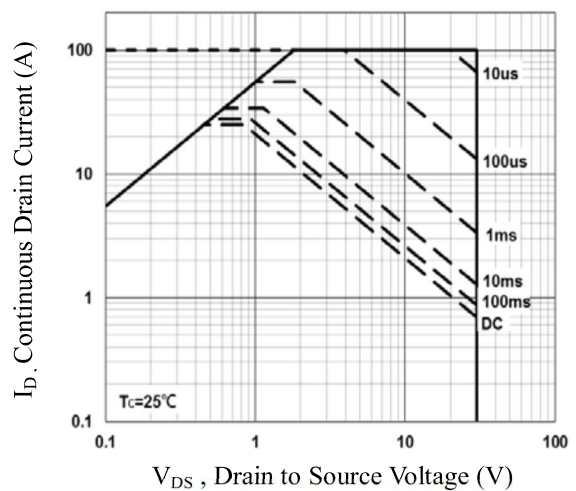
**Fig.3 Normalized  $V_{th}$  vs.  $T_j$**



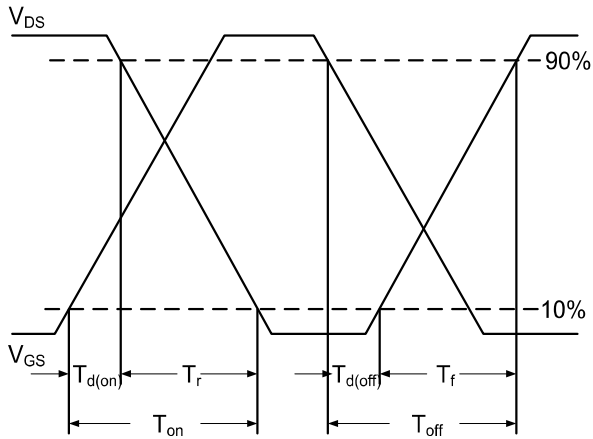
**Fig.4 Gate Charge Waveform**



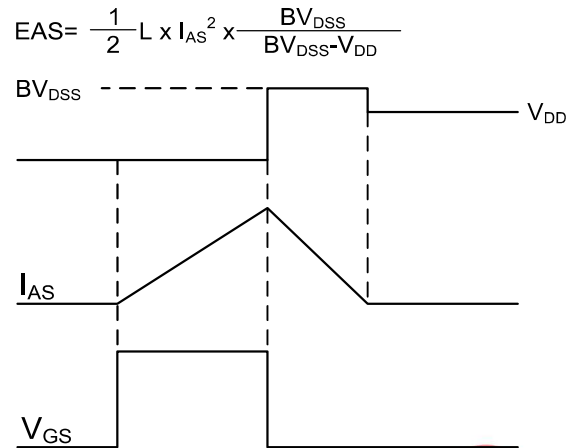
**Fig.5 Normalized Transient Response**



**Fig.6 Maximum Safe Operation Area**



**Fig.7 Switching Time Waveform**



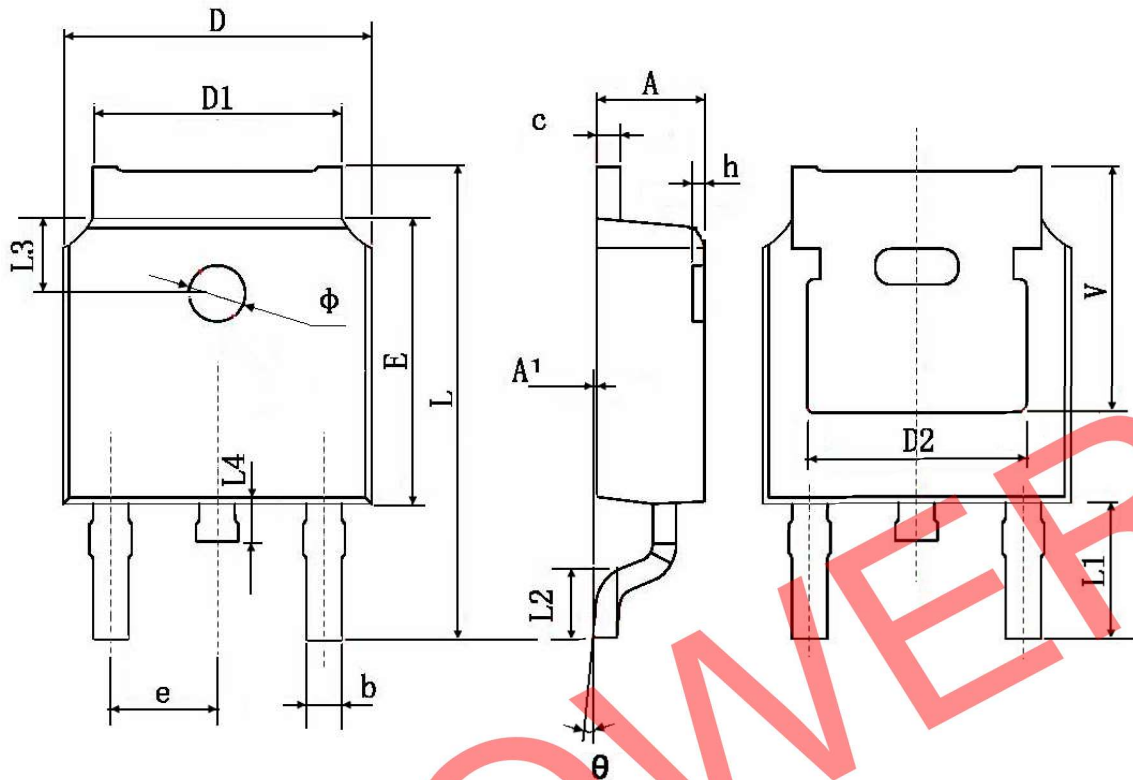
**Fig.8 EAS Waveform**

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**AP30N03K**

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**TO-252 Package Information**



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.660	0.860	0.026	0.034
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	4.830 TYP.		0.190 TYP.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.800	10.400	0.386	0.409
L1	2.900 TYP.		0.114 TYP.	
L2	1.400	1.700	0.055	0.067
L3	1.600 TYP.		0.063 TYP.	
L4	0.600	1.000	0.024	0.039
phi	1.100	1.300	0.043	0.051
theta	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.350 TYP.		0.211 TYP.	